STMicroelectronics - <u>STM32L152VCT6D Datasheet</u>



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Applications of "<u>Embedded -</u> <u>Microcontrollers</u>"

Details

Product Status	Active
Core Processor	ARM® Cortex®-M3
Core Size	32-Bit Single-Core
Speed	32MHz
Connectivity	I ² C, IrDA, LINbus, SPI, UART/USART, USB
Peripherals	Cap Sense, DMA, I ² S, LCD, POR, PWM, WDT
Number of I/O	83
Program Memory Size	256KB (256K x 8)
Program Memory Type	FLASH
EEPROM Size	8K x 8
RAM Size	32K x 8
Voltage - Supply (Vcc/Vdd)	1.65V ~ 3.6V
Data Converters	A/D 25x12b; D/A 2x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	100-LQFP
Supplier Device Package	100-LQFP (14x14)
Purchase URL	https://www.e-xfl.com/product-detail/stmicroelectronics/stm32l152vct6d

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Figure 46.	UFBGA100, 7 x 7 mm, 0.5 mm pitch, package top view example	124
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1 Introduction

This datasheet provides the ordering information and mechanical device characteristics of the STM32L151xC and STM32L152xC ultra-low-power ARM[®] Cortex[®]-M3 based microcontroller product line with a Flash memory of 256 Kbytes.

The ultra-low-power STM32L151xC and STM32L152xC family includes devices in 6 different package types: from 48 pins to 100 pins. Depending on the device chosen, different sets of peripherals are included, the description below gives an overview of the complete range of peripherals proposed in this family.

These features make the ultra-low-power STM32L151xC and STM32L152xC microcontroller family suitable for a wide range of applications:

- Medical and handheld equipment
- Application control and user interface
- PC peripherals, gaming, GPS and sport equipment
- Alarm systems, wired and wireless sensors, video intercom
- Utility metering

This STM32L151xC and STM32L152xC datasheet should be read in conjunction with the STM32L1xxxx reference manual (RM0038). The application note "Getting started with STM32L1xxxx hardware development" (AN3216) gives a hardware implementation overview. Both documents are available from the STMicroelectronics website *www.st.com*.

For information on the ARM[®] Cortex[®]-M3 core please refer to the ARM[®] Cortex[®]-M3 technical reference manual, available from the www.arm.com website. *Figure 1* shows the general block diagram of the device family.



2.1 Device overview

Table 2. Ultra-low-power STM32L151xC and STM32L152xC device features and peripheral counts

Periphe	ral	STM32L15xCC	STM32L15xUC STM32L15xRC	STM32L15xVC			
Flash (Kbytes)		256					
Data EEPROM (Kb	oytes)		8				
RAM (Kbytes)			32				
	32 bit		1				
Timers	General- purpose		6				
	Basic		2				
	SPI		8(3) ⁽¹⁾				
	I ² S		2				
Communica tion interfaces	l ² C	2					
	USART	3					
	USB	1					
GPIOs		37	51	83			
Operation amplifie	ers	2					
12-bit synchronize Number of channe		1 14					
12-bit DAC Number of channe	els	2 2					
LCD ⁽²⁾ COM x SEG		1 4x18	1 4x32 or 8x28	1 4x44 or 8x40			
Comparators			2				
Capacitive sensin	g channels	16	16 23				
Max. CPU frequen	су	32 MHz					
Operating voltage		1.8 V to 3.6 V (down to 1.65 V at power-down) with BOR option 1.65 V to 3.6 V without BOR option					
Operating temperating	atures	Ambient operating temperature: -40 °C to 85 °C / -40 °C to 105 °C Junction temperature: -40 to + 110 °C					
Packages		LQFP48, UFQFPN48	LQFP64, WLCSP63	LQFP100, UFBGA100			

1. 5 SPIs are USART configured in synchronous mode emulating SPI master.

2. STM32L152xx devices only.



3.7 Memories

The STM32L151xC and STM32L152xC devices have the following features:

- 32 Kbytes of embedded RAM accessed (read/write) at CPU clock speed with 0 wait states. With the enhanced bus matrix, operating the RAM does not lead to any performance penalty during accesses to the system bus (AHB and APB buses).
- The non-volatile memory is divided into three arrays:
 - 256 Kbytes of embedded Flash program memory
 - 8 Kbytes of data EEPROM
 - Options bytes

The options bytes are used to write-protect or read-out protect the memory (with 4 Kbytes granularity) and/or readout-protect the whole memory with the following options:

- Level 0: no readout protection
- Level 1: memory readout protection, the Flash memory cannot be read from or written to if either debug features are connected or boot in RAM is selected
- Level 2: chip readout protection, debug features (ARM Cortex-M3 JTAG and serial wire) and boot in RAM selection disabled (JTAG fuse)

The whole non-volatile memory embeds the error correction code (ECC) feature.

The user area of the Flash memory can be protected against Dbus read access by PCROP feature (see RM0038 for details).

3.8 DMA (direct memory access)

The flexible 12-channel, general-purpose DMA is able to manage memory-to-memory, peripheral-to-memory and memory-to-peripheral transfers. The DMA controller supports circular buffer management, avoiding the generation of interrupts when the controller reaches the end of the buffer.

Each channel is connected to dedicated hardware DMA requests, with software trigger support for each channel. Configuration is done by software and transfer sizes between source and destination are independent.

The DMA can be used with the main peripherals: SPI, I^2C , USART, general-purpose timers, DAC and ADC.



introduced by the finger (or any conductive object) is measured using a proven implementation based on a surface charge transfer acquisition principle. It consists of charging the sensor capacitance and then transferring a part of the accumulated charges into a sampling capacitor until the voltage across this capacitor has reached a specific threshold. The capacitive sensing acquisition only requires few external components to operate. This acquisition is managed directly by the GPIOs, timers and analog I/O groups (see Section 3.14: System configuration controller and routing interface).

Reliable touch sensing functionality can be quickly and easily implemented using the free STM32L1xx STMTouch touch sensing firmware library.

3.16 Timers and watchdogs

The ultra-low-power STM32L151xC and STM32L152xC devices include seven generalpurpose timers, two basic timers, and two watchdog timers.

Table 7 compares the features of the general-purpose and basic timers.

Timer	Counter resolution	Counter type	Prescaler factor	DMA request generation	Capture/compare channels	Complementary outputs			
TIM2, TIM3, TIM4	16-bit	Up, down, up/down	Any integer between 1 and 65536	Yes	4	No			
TIM5	32-bit	Up, down, up/down	Any integer between 1 and 65536	Yes	4	No			
TIM9	16-bit	Up, down, up/down	Any integer between 1 and 65536	No	2	No			
TIM10, TIM11	16-bit	Up	Any integer between 1 and 65536	No	1	No			
TIM6, TIM7	16-bit	Up	Any integer between 1 and 65536	Yes	0	No			

Table 7. Timer feature comparison

3.16.1 General-purpose timers (TIM2, TIM3, TIM4, TIM5, TIM9, TIM10 and TIM11)

There are seven synchronizable general-purpose timers embedded in the STM32L151xC and STM32L152xC devices (see *Table 7* for differences).

TIM2, TIM3, TIM4, TIM5

TIM2, TIM3, TIM4 are based on 16-bit auto-reload up/down counter. TIM5 is based on a 32bit auto-reload up/down counter. They include a 16-bit prescaler. They feature four independent channels each for input capture/output compare, PWM or one-pulse mode output. This gives up to 16 input captures/output compares/PWMs on the largest packages.

TIM2, TIM3, TIM4, TIM5 general-purpose timers can work together or with the TIM10, TIM11 and TIM9 general-purpose timers via the Timer Link feature for synchronization or event chaining. Their counter can be frozen in debug mode. Any of the general-purpose timers can be used to generate PWM outputs.

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3.17.2 Universal synchronous/asynchronous receiver transmitter (USART)

The three USART interfaces are able to communicate at speeds of up to 4 Mbit/s. They support IrDA SIR ENDEC and have LIN Master/Slave capability. The three USARTs provide hardware management of the CTS and RTS signals and are ISO 7816 compliant.

All USART interfaces can be served by the DMA controller.

3.17.3 Serial peripheral interface (SPI)

Up to three SPIs are able to communicate at up to 16 Mbits/s in slave and master modes in full-duplex and half-duplex communication modes. The 3-bit prescaler gives 8 master mode frequencies and the frame is configurable to 8 bits or 16 bits. The hardware CRC generation/verification supports basic SD Card/MMC modes.

The SPIs can be served by the DMA controller.

3.17.4 Inter-integrated sound (I²S)

Two standard I2S interfaces (multiplexed with SPI2 and SPI3) are available. They can operate in master or slave mode, and can be configured to operate with a 16-/32-bit resolution as input or output channels. Audio sampling frequencies from 8 kHz up to 192 kHz are supported. When either or both of the I2S interfaces is/are configured in master mode, the master clock can be output to the external DAC/CODEC at 256 times the sampling frequency.

The I2Ss can be served by the DMA controller.

3.17.5 Universal serial bus (USB)

The STM32L151xC and STM32L152xC devices embed a USB device peripheral compatible with the USB full-speed 12 Mbit/s. The USB interface implements a full-speed (12 Mbit/s) function interface. It has software-configurable endpoint setting and supports suspend/resume. The dedicated 48 MHz clock is generated from the internal main PLL (the clock source must use a HSE crystal oscillator).

3.18 CRC (cyclic redundancy check) calculation unit

The CRC (cyclic redundancy check) calculation unit is used to get a CRC code from a 32-bit data word and a fixed generator polynomial.

Among other applications, CRC-based techniques are used to verify data transmission or storage integrity. In the scope of the EN/IEC 60335-1 standard, they offer a means of verifying the Flash memory integrity. The CRC calculation unit helps compute a signature of the software during runtime, to be compared with a reference signature generated at link-time and stored at a given memory location.

Table 9. STM32L151xC and STM32L152xC pin definitions (continued) Pins Pin functions								•		
	F	rins							Pin fun	ctions
UFBGA100	LQFP100	LQFP64	WLCSP63	LQFP48 or UFQFPN48	Pin name	Pin type ⁽¹⁾	I / O Structure	Main function ⁽²⁾ (after reset)	Alternate functions	Additional functions
C1	7	2	D5	2	PC13- WKUP2	I/O	FT	PC13	-	WKUP2/ RTC_TAMP1/ RTC_TS/RTC_OUT
D1	8	3	D7	3	PC14- OSC32_IN ⁽⁴⁾	I/O	тс	PC14	-	OSC32_IN
E1	9	4	D6	4	PC15- OSC32_OUT	I/O	тс	PC15	-	OSC32_OUT
F2	10	-	-	-	V _{SS_5}	S	-	V _{SS_5}	-	-
G2	11	-	-	-	V_{DD_5}	S	-	V _{DD_5}	-	-
F1	12	5	F6	5	PH0- OSC_IN ⁽⁵⁾	I/O	тс	PH0	-	OSC_IN
G1	13	6	F7	6	PH1- OSC_OUT ⁽⁵⁾	I/O	тс	PH1	-	OSC_OUT
H2	14	7	E7	7	NRST	I/O	RST	NRST	-	-
H1	15	8	E6	-	PC0	I/O	FT	PC0	LCD_SEG18	ADC_IN10/ COMP1_INP
J2	16	9	E5	-	PC1	I/O	FT	PC1	LCD_SEG19	ADC_IN11/ COMP1_INP
J3	17	10	G7	-	PC2	I/O	FT	PC2	LCD_SEG20	ADC_IN12/ COMP1_INP
K2	18	11	G6	-	PC3	I/O	тс	PC3	LCD_SEG21	ADC_IN13/ COMP1_INP
J1	19	12	F5	8	V _{SSA}	S	-	V _{SSA}	-	-
K1	20	-	-	-	V _{REF-}	S	-	V _{REF-}	-	-
L1	21	-	-	-	V _{REF+}	S	-	V _{REF+}	-	-
M1	22	13	H7	9	V _{DDA}	S	-	V _{DDA}	-	-
L2	23	14	E4	10	PA0-WKUP1	I/O	FT	PA0	TIM2_CH1_ETR/ TIM5_CH1/ USART2_CTS	WKUP1/ RTC_TAMP2/ ADC_IN0/ COMP1_INP

Table 9. STM32L151xC and STM32L152xC pin definitions (continued)



5. To guarantee less than 1% VREF_OUT deviation.

6.3.4 Supply current characteristics

The current consumption is a function of several parameters and factors such as the operating voltage, temperature, I/O pin loading, device software configuration, operating frequencies, I/O pin switching rate, program location in memory and executed binary code. The current consumption is measured as described in *Figure 14: Current consumption measurement scheme*.

All Run-mode current consumption measurements given in this section are performed with a reduced code that gives a consumption equivalent to the Dhrystone 2.1 code, unless otherwise specified. The current consumption values are derived from tests performed under ambient temperature $T_A = 25$ °C and V_{DD} supply voltage conditions summarized in *Table 14: General operating conditions*, unless otherwise specified.

The MCU is placed under the following conditions:

- All I/O pins are configured in analog input mode
- All peripherals are disabled except when explicitly mentioned.
- The Flash memory access time, 64-bit access and prefetch is adjusted depending on f_{HCLK} frequency and voltage range to provide the best CPU performance.
- When the peripherals are enabled $f_{APB1} = f_{APB2} = f_{AHB}$.
- When PLL is ON, the PLL inputs are equal to HSI = 16 MHz (if internal clock is used) or HSE = 16 MHz (if HSE bypass mode is used).
- The HSE user clock applied to OSCI_IN input follows the characteristic specified in *Table 27: High-speed external user clock characteristics*.
- For maximum current consumption $V_{DD} = V_{DDA} = 3.6$ V is applied to all supply pins.
- For typical current consumption V_{DD} = V_{DDA} = 3.0 V is applied to all supply pins if not specified otherwise.



Symbol	Parameter		Conditions	Тур	Max ⁽¹⁾	Unit	
				$T_A = -40 \ ^\circ C$ to 25 $^\circ C$	8.6	12	
			MSI clock, 65 kHz f _{HCLK} = 32 kHz	T _A = 85 °C	19	25	
		All peripherals		T _A = 105 °C	35	47	
		OFF, code		$T_A = -40 \text{ °C to } 25 \text{ °C}$	14	16	
		executed from RAM,	MSI clock, 65 kHz f _{HCLK} = 65 kHz	T _A = 85 °C	24	29	
		Flash switched		T _A = 105 °C	40	51	
		OFF, V _{DD}		$T_A = -40 \degree C$ to 25 $\degree C$	26	29	
		from 1.65 V to 3.6 V	MSI clock, 131 kHz	T _A = 55 °C	28	31	
	Supply current in Low-power run mode	10 3.0 V	f _{HCLK} = 131 kHz	T _A = 85 °C	36	42	μA
I _{DD (LP}				T _A = 105 °C	52	64	
Run)		All	MSI clock, 65 kHz f _{HCLK} = 32 kHz	$T_A = -40 \degree C$ to 25 $\degree C$	20	24	
				T _A = 85 °C	32	37	
				T _A = 105 °C	49	61	
		peripherals	MSI clock, 65 kHz f _{HCLK} = 65 kHz	$T_A = -40 \ ^\circ C$ to 25 $^\circ C$	26	30	
		OFF, code executed		T _A = 85 °C	38	44	
		from Flash,		T _A = 105 °C	55	67	
		V _{DD} from 1.65 V to		$T_A = -40 \ ^\circ C$ to 25 $^\circ C$	41	46	
		3.6 V	MSI clock, 131 kHz	T _A = 55 °C	44	50	
			f _{HCLK} = 131 kHz	T _A = 85 °C	56	87	
				T _A = 105 °C	73	110	
I _{DD} max (LP Run)	Max allowed current in Low-power run mode	V _{DD} from 1.65 V to 3.6 V	-	-	-	200	

Table 21. Current consumption in Low-power run mode

1. Guaranteed by characterization results, unless otherwise specified.



Symbol	Parameter	С	onditions		Тур	Max ⁽¹⁾	Unit
				T _A = -40°C to 25°C V _{DD} = 1.8 V	1.15	-	
			LCD	$T_A = -40^{\circ}C$ to $25^{\circ}C$	1.4	-	
			OFF	T _A = 55°C	2	-	
				T _A = 85°C	3.4	10	
		RTC clocked by LSI or LSE external clock		T _A = 105°C	6.35	23	
		(32.768kHz),	LCD	$T_A = -40^{\circ}C$ to $25^{\circ}C$	1.55	6	
		regulator in LP mode, HSI and HSE OFF	ON	T _A = 55°C	2.15	7	
		(no independent	(static duty) ⁽²⁾	T _A = 85°C	3.55	12	
		watchdog)	uuty).	T _A = 105°C	6.3	27	
				$T_A = -40^{\circ}C$ to $25^{\circ}C$	3.9	10	
	Supply current in Stop mode with RTC enabled		LCD ON (1/8 duty) ⁽³⁾	T _A = 55°C	4.65	11	-
				T _A = 85°C	6.25	16	
				T _A = 105°C	9.1	44	
		RTC clocked by LSE	LCD OFF	$T_A = -40^{\circ}C$ to $25^{\circ}C$	1.5	-	
I _{DD} (Stop with RTC)				T _A = 55°C	2.15	-	μΑ
with IXIC)				T _A = 85°C	3.7	-	
				T _A = 105°C	6.75	-	
			LCD ON (static duty) ⁽²⁾	$T_A = -40^{\circ}C$ to $25^{\circ}C$	1.6	-	
				T _A = 55°C	2.3	-	
				T _A = 85°C	3.8	-	
		external quartz (32.768kHz),	uuty)()	T _A = 105°C	6.85	-	
		regulator in LP mode,		$T_A = -40^{\circ}C$ to $25^{\circ}C$	4	-	
		HSI and HSE OFF (no independent	LCD ON (1/8	T _A = 55°C	4.85	-	
		watchdog ⁽⁴⁾	duty) ⁽³⁾	T _A = 85°C	6.5	-	
				T _A = 105°C	9.1	-	1
				$T_A = -40^{\circ}C \text{ to } 25^{\circ}C$ $V_{DD} = 1.8V$	1.2	-	
			LCD OFF	$T_A = -40^{\circ}C \text{ to } 25^{\circ}C$ $V_{DD} = 3.0V$	1.5	-	
				$T_A = -40^{\circ}C \text{ to } 25^{\circ}C$ $V_{DD} = 3.6V$	1.75	-	



Symbol	Parameter	Conditions	i	Тур	Max ⁽¹⁾	Unit
		Regulator in LP mode, HSI and HSE OFF, independent watchdog and LSI enabled	$T_A = -40^{\circ}C$ to 25°C	1.8	2.2	
I _{DD} (Stop)	Supply current in Stop mode (RTC disabled)		$T_A = -40^{\circ}C$ to $25^{\circ}C$	0.435	1	μA
.00(Regulator in LP mode, LSI, HSI and HSE OFF (no independent watchdog)	T _A = 55°C	0.99	3	
			T _A = 85°C	2.4	9	
			T _A = 105°C	5.5	22 ⁽⁵⁾	
I _{DD}	Supply current during	MSI = 4.2 MHz		2	-	
(WU from Stop)	wakeup from Stop mode	MSI = 1.05 MHz	$T_A = -40^{\circ}C$ to $25^{\circ}C$	1.45	-	mA
		MSI = 65 kHz ⁽⁶⁾		1.45	-	

Table 23. Typical and maximum current cor	sumptions in Stop mode (continued)
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1. Guaranteed by characterization results, unless otherwise specified.

2. LCD enabled with external VLCD, static duty, division ratio = 256, all pixels active, no LCD connected.

3. LCD enabled with external VLCD, 1/8 duty, 1/3 bias, division ratio = 64, all pixels active, no LCD connected.

4. Based on characterization done with a 32.768 kHz crystal (MC306-G-06Q-32.768, manufacturer JFVNY) with two 6.8 pF loading capacitors.

5. Guaranteed by test in production.

When MSI = 64 kHz, the RMS current is measured over the first 15 µs following the wakeup event. For the remaining part
of the wakeup period, the current corresponds the Run mode current.



Symbol	Parameter	Conditions	Min	Тур	Мах	Unit
f _{OSC_IN}	Oscillator frequency	-	1		24	MHz
R _F	Feedback resistor	-	-	200	-	kΩ
С	Recommended load capacitance versus equivalent serial resistance of the crystal $(R_S)^{(3)}$	R _S = 30 Ω	-	20	-	pF
I _{HSE}	HSE driving current	V_{DD} = 3.3 V, V_{IN} = V_{SS} with 30 pF load	-	-	3	mA
	HSE oscillator power	C = 20 pF f _{OSC} = 16 MHz	-	-	2.5 (startup) 0.7 (stabilized)	mA
I _{DD(HSE)}	consumption	C = 10 pF f _{OSC} = 16 MHz	-	-	2.5 (startup) 0.46 (stabilized)	
9 _m	Oscillator transconductance	Startup	3.5	-	-	mA /V
t _{SU(HSE)} ⁽⁴⁾	Startup time	V _{DD} is stabilized	-	1	-	ms

Table 29. HSE oscillator characteristics⁽¹⁾⁽²⁾

1. Resonator characteristics given by the crystal/ceramic resonator manufacturer.

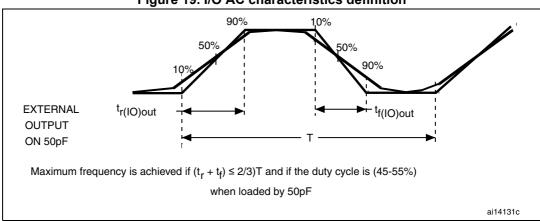
2. Guaranteed by characterization results.

 The relatively low value of the RF resistor offers a good protection against issues resulting from use in a humid environment, due to the induced leakage and the bias condition change. However, it is recommended to take this point into account if the MCU is used in tough humidity conditions.

4. t_{SU(HSE)} is the startup time measured from the moment it is enabled (by software) to a stabilized 8 MHz oscillation is reached. This value is measured for a standard crystal resonator and it can vary significantly with the crystal manufacturer.

For C_{L1} and C_{L2} , it is recommended to use high-quality external ceramic capacitors in the 5 pF to 25 pF range (typ.), designed for high-frequency applications, and selected to match the requirements of the crystal or resonator (see *Figure 17*). C_{L1} and C_{L2} are usually the same size. The crystal manufacturer typically specifies a load capacitance which is the series combination of C_{L1} and C_{L2} . PCB and MCU pin capacitance must be included (10 pF can be used as a rough estimate of the combined pin and board capacitance) when sizing C_{L1} and C_{L2} . Refer to the application note AN2867 "Oscillator design guide for ST microcontrollers" available from the ST website *www.st.com*.







6.3.14 NRST pin characteristics

The NRST pin input driver uses CMOS technology. It is connected to a permanent pull-up resistor, R_{PU} (see *Table 46*)

Unless otherwise specified, the parameters given in *Table 46* are derived from tests performed under the conditions summarized in *Table 14*.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{IL(NRST)} ⁽¹⁾	NRST input low level voltage	-	-	-	0.3 V _{DD}	
V _{IH(NRST)} ⁽¹⁾	NRST input high level voltage	-	0.39V _{DD} +0.59	-	-	V
V _{OL(NRST)} ⁽¹⁾	NRST output low	I _{OL} = 2 mA 2.7 V < V _{DD} < 3.6 V	-	-	0.4	v
VOL(NRST)	level voltage	I _{OL} = 1.5 mA 1.65 V < V _{DD} < 2.7 V	-	-	0.4	
V _{hys(NRST)} ⁽¹⁾	NRST Schmitt trigger voltage hysteresis	-	-	10%V _{DD} ⁽²⁾	-	mV
R _{PU}	Weak pull-up equivalent resistor ⁽³⁾	$V_{IN} = V_{SS}$	30	45	60	kΩ
V _{F(NRST)} ⁽¹⁾	NRST input filtered pulse	-	-	-	50	ns
V _{NF(NRST)} ⁽³⁾	NRST input not filtered pulse	-	350	-	-	ns

Table 46. NRST pin characteristics

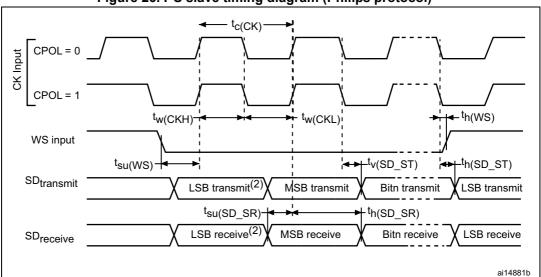
1. Guaranteed by design.

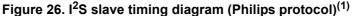
2. With a minimum of 200 mV.

3. The pull-up is designed with a true resistance in series with a switchable PMOS. This PMOS contribution to the series resistance is around 10%.



ODD bit value, digital contribution leads to a min of (I2SDIV/(2*I2SDIV+ODD) and a max of (I2SDIV+ODD)/(2*I2SDIV+ODD). Fs max is supported for each mode/condition.





- 1. Measurement points are done at CMOS levels: 0.3 × V_{DD} and 0.7 × V_{DD} .
- 2. LSB transmit/receive of the previously transmitted byte. No LSB transmit/receive is sent before the first byte.

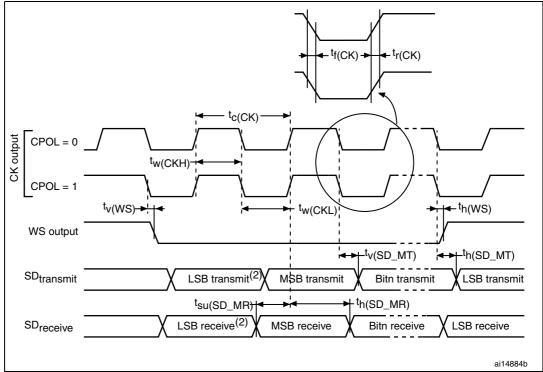


Figure 27. I²S master timing diagram (Philips protocol)⁽¹⁾

- 1. Guaranteed by characterization results.
- 2. LSB transmit/receive of the previously transmitted byte. No LSB transmit/receive is sent before the first byte.



6.3.17 12-bit ADC characteristics

Unless otherwise specified, the parameters given in *Table 56* are guaranteed by design.

Symbol	Parameter		Conditions	Min	Max	Unit	
f _{ADC}		Voltage range 1 & 2	2.4 V ≤V _{DDA} ≤3.6 V	V _{REF+} = V _{DDA}	0.480	16	MHz
				V _{REF+} < V _{DDA} V _{REF+} > 2.4 V		8	
				V _{REF+} < V _{DDA} V _{REF+} ≤2.4 V		4	
			191101 011	V _{REF+} = V _{DDA}		8	
			1.8 V ≤V _{DDA} ≤2.4 V	V _{REF+} < V _{DDA}		4	
			Voltage range 3			4	

Table 55. ADC clock frequence	:v
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Table 56. ADC characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit		
V_{DDA}	Power supply	-	1.8	-	3.6			
V _{REF+}	Positive reference voltage	-	1.8 ⁽¹⁾	-	V _{DDA}	V		
V _{REF-}	Negative reference voltage	-	-	V _{SSA}	-	1		
I _{VDDA}	Current on the V _{DDA} input pin	-	-	1000	1450			
ı (2)	Current on the V input nin	Peak	-	400	700	μA		
I _{VREF} ⁽²⁾	Current on the V _{REF} input pin	Average	-	400	450			
V _{AIN}	Conversion voltage range ⁽³⁾	-	0 ⁽⁴⁾	-	V _{REF+}	V		
fs	12 hit compling rate	Direct channels	-	-	1	Mana		
	12-bit sampling rate	Multiplexed channels	-	-	0.76	- Msps		
	10 hit compling rate	Direct channels	-	-	1.07	Mana		
	10-bit sampling rate	Multiplexed channels	-	-	0.8	- Msps		
	0 hit compliant rate	Direct channels	-	-	1.23	Mana		
	8-bit sampling rate	Multiplexed channels	-	-	0.89	Msps		
	6 bit compling rate	Direct channels	-	-	1.45	Mana		
	6-bit sampling rate	Multiplexed channels	-	-	1	- Msps		



Symbol	Parameter	Conditions	Min	Тур	Max	Unit	
dOffset/dT ⁽¹⁾	Offset error temperature	$V_{DDA} = 3.3V$ $V_{REF+} = 3.0V$ $T_A = 0$ to 50 ° C DAC output buffer OFF	-20	-10	0	μV/°C	
	coefficient (code 0x800)	$V_{DDA} = 3.3V$ $V_{REF+} = 3.0V$ $T_A = 0 \text{ to } 50 ^{\circ}\text{C}$ DAC output buffer ON	0	20	50	μν/ Ο	
Gain ⁽¹⁾	Gain error ⁽⁷⁾	$C_L \le 50 \text{ pF}, R_L \ge 5 \text{ k}\Omega$ DAC output buffer ON	-	+0.1 / -0.2%	+0.2 / -0.5%		
Gain	Gamenor	No R_L , $C_L \le 50 \text{ pF}$ DAC output buffer OFF	-	+0 / -0.2%	+0 / -0.4%	%	
dGain/dT ⁽¹⁾	Gain error temperature	$V_{DDA} = 3.3V$ $V_{REF+} = 3.0V$ $T_A = 0 \text{ to } 50 ^{\circ}\text{C}$ DAC output buffer OFF	-10	-2	0	μV/°C	
dGain/d I (1)	coefficient	$V_{DDA} = 3.3V$ $V_{REF+} = 3.0V$ $T_A = 0 \text{ to } 50 ^{\circ}\text{C}$ DAC output buffer ON	-40	-8	0		
TUE ⁽¹⁾	Total unadjusted error	$C_{L} \le 50 \text{ pF}, R_{L} \ge 5 \text{ k}\Omega$ DAC output buffer ON	-	12	30	LSB	
		No R_L , $C_L \le 50 \text{ pF}$ DAC output buffer OFF	-	8	12		
t _{SETTLING}	Settling time (full scale: for a 12-bit code transition between the lowest and the highest input codes till DAC_OUT reaches final value ±1LSB	C_L ≤ 50 pF, R_L ≥ 5 kΩ	-	7	12	μs	
Update rate	Max frequency for a correct DAC_OUT change (95% of final value) with 1 LSB variation in the input code	C_L ≤ 50 pF, R_L ≥ 5 kΩ	-	-	1	Msps	
twakeup	Wakeup time from off state (setting the ENx bit in the DAC Control register) ⁽⁸⁾	$C_L \le 50 \text{ pF, } R_L \ge 5 \text{ k}\Omega$	-	9	15	μs	
PSRR+	V _{DDA} supply rejection ratio (static DC measurement)	$C_L \le 50 \text{ pF, } R_L \ge 5 \text{ k}\Omega$	-	-60	-35	dB	

1. Data based on characterization results.

2. Connected between DAC_OUT and $\mathsf{V}_{\mathsf{SSA}}.$

3. Difference between two consecutive codes - 1 LSB.

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7.2 LQFP64, 10 x 10 mm, 64-pin low-profile quad flat package information

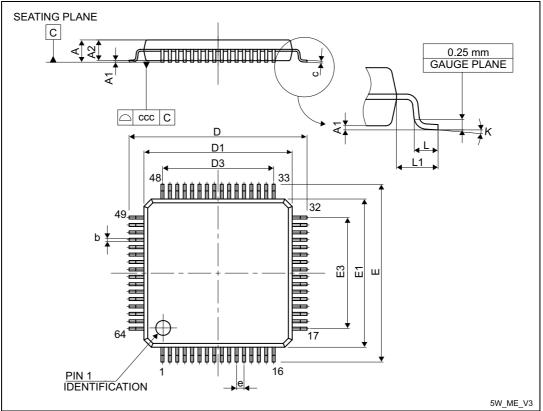


Figure 35. LQFP64, 10 x 10 mm, 64-pin low-profile quad flat package outline

1. Drawing is not to scale.

Table 67. LQFP64, 10 x 10 mm 64-pin low-profile quad flat package mechanical
data

			uata			
Symbol		millimeters		inches ⁽¹⁾		
Symbol	Min	Тур	Мах	Min	Тур	Мах
А	-	-	1.600	-	-	0.0630
A1	0.050	-	0.150	0.0020	-	0.0059
A2	1.350	1.400	1.450	0.0531	0.0551	0.0571
b	0.170	0.220	0.270	0.0067	0.0087	0.0106
С	0.090	-	0.200	0.0035	-	0.0079
D	-	12.000	-	-	0.4724	-
D1	-	10.000	-	-	0.3937	-
D3	-	7.500	-	-	0.2953	-
Е	-	12.000	-	-	0.4724	-
E1	-	10.000	-	-	0.3937	-



7.4 UFQFPN48 7 x 7 mm, 0.5 mm pitch, package information

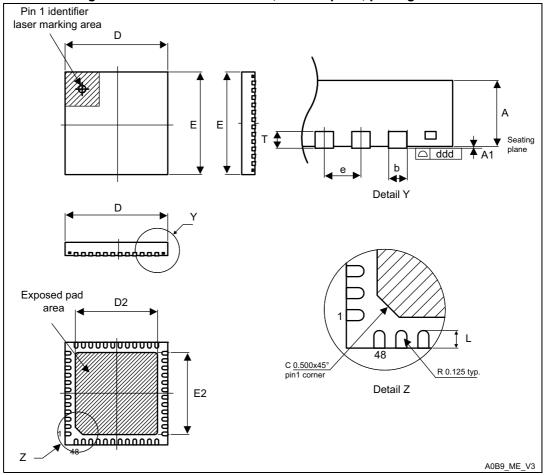


Figure 41. UFQFPN48 7 x 7 mm, 0.5 mm pitch, package outline

1. Drawing is not to scale.

- 2. All leads/pads should also be soldered to the PCB to improve the lead/pad solder joint life.
- 3. There is an exposed die pad on the underside of the UFQFPN package. It is recommended to connect and solder this back-side pad to PCB ground.



Symbol		millimeters		inches ⁽¹⁾		
Symbol	Min	Тур	Мах	Min	Тур	Мах
А	0.500	0.550	0.600	0.0197	0.0217	0.0236
A1	0.000	0.020	0.050	0.0000	0.0008	0.0020
D	6.900	7.000	7.100	0.2717	0.2756	0.2795
E	6.900	7.000	7.100	0.2717	0.2756	0.2795
D2	5.500	5.600	5.700	0.2165	0.2205	0.2244
E2	5.500	5.600	5.700	0.2165	0.2205	0.2244
L	0.300	0.400	0.500	0.0118	0.0157	0.0197
Т	-	0.152	-	-	0.0060	-
b	0.200	0.250	0.300	0.0079	0.0098	0.0118
е	-	0.500	-	-	0.0197	-
ddd	-	-	0.080	-	-	0.0031

Table 69. UFQFPN48 – ultra thin fine pitch quad flat pack no-lead 7 × 7 mm,0.5 mm pitch package mechanical data

1. Values in inches are converted from mm and rounded to 4 decimal digits.

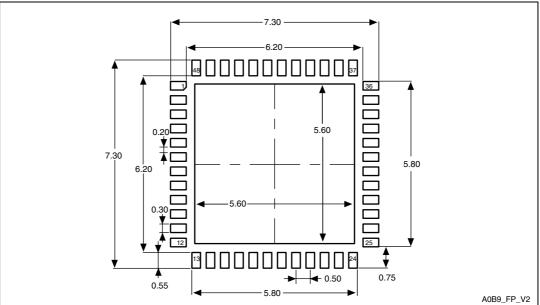


Figure 42. UFQFPN48 recommended footprint

1. Dimensions are in millimeters.



Symbol		millimeters		inches ⁽¹⁾		
	Min	Тур	Мах	Min	Тур	Мах
eee	-	-	0.150	-	-	0.0059
fff	-	-	0.050	-	-	0.0020

Table 70. UFBGA100, 7 x 7 mm, 0.5 mm pitch package mechanical data (continued)

1. Values in inches are converted from mm and rounded to 4 decimal digits.

Figure 45. UFBGA100, 7 x 7 mm, 0.5 mm pitch, package recommended footprint

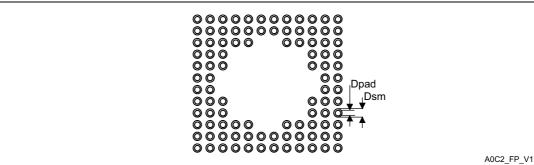


Table 71. UFBGA100, 7 x 7 mm, 0.50 mm pitch, recommended PCB design rules

Dimension	Recommended values		
Pitch	0.5		
Dpad	0.280 mm		
Dsm	0.370 mm typ. (depends on the soldermask registration tolerance)		
Stencil opening	0.280 mm		
Stencil thickness	Between 0.100 mm and 0.125 mm		

